

MBR10200FCT Schottky Diodes

Features

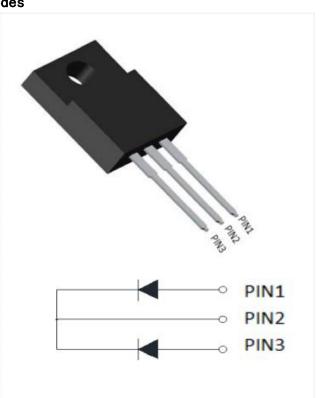
- High efficiency operation
- Guard ring for enhanced ruggedness and long term reliablity
- High purity,high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Solder dip maximum peak of 275 °C /7s, per JESD 22-B106

Typical Application

For use in switching power supplies, converters, freewheeling diodes and reverse battery protection.

Mechanical Data

- Package: ITO-220AB
 Molding compound meets UL 94 V-0 flammability rating,RoHS-compliant
- Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- Polarity: Color Band denotes cathode end



■ Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	Symbol	Unit	Conditions	MBR10200FCT	
Repetitive Peak Reverse Voltage	V_{RRM}	V		200	
Average Rectified Output Current	Io	Α	60HZ Half-sine wave, Resistance load, Tc(Fig.1)	10	
Surge(Nonrepetitive)Forward Current	I _{FSM}	Α	60HZ sine wave, 1 cycle, Ta=25℃	100	
Current Squared Time	l _{2t}	A ² s	1ms≤t<8.3ms Tj=25℃,Rating of per diode	41	
Storage Temperature	T _{stg}	$^{\circ}$		-55 ~ +150	
Junction Temperature	Tj		IN DC Forward Mode-Forward Operations, without reverse bias, t ≤1 h (Fig. 1)①	-55 ~ + 150	

■ Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	Symbol	Unit	Conditions		MBR10200FCT
Peak Forward Voltage	V _{FM}	V	I _{FM} =5A		0.95
Peak Reverse Current	I _{RRM1}	· mA	V _{RM} =V _{RRM}	Ta=25℃	0.05
	I _{RRM2}			Ta=100℃	1
Thermal Resistance	R _{0J-C}	°C/W	Between junction and case		2.0

Revised: 2021-11-29

NOTES:

Meets the requirement of IEC 61215 Ed.2 byqass diode thermal test

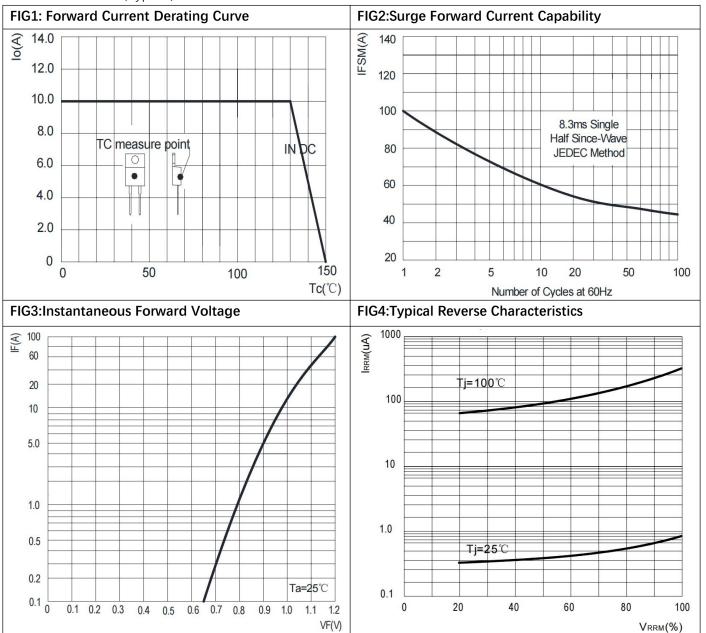






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■ Characteristics (Typical)



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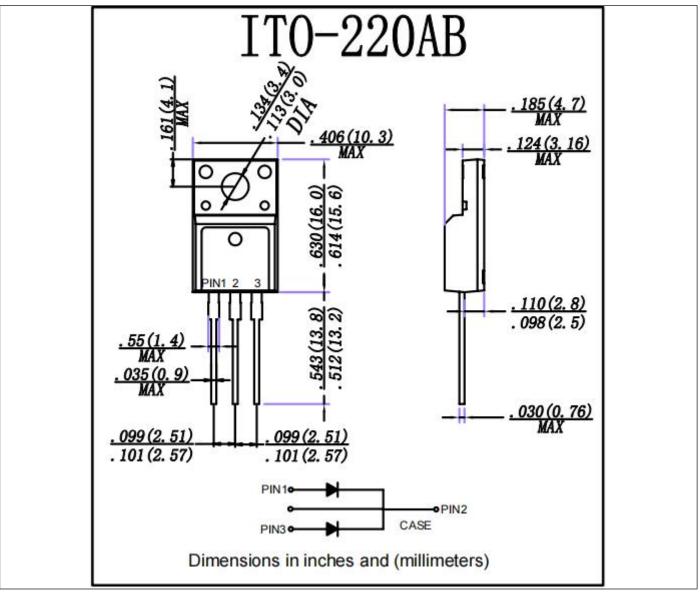


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■ Ordering Information (Example)

PREFERED	PACKAGE CODE	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR10200FCT	ITO-220AB	50	1000	5000	Tube

■ Outline Dimensions



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